

In the Claims

Please replace all prior versions of claims in the application with the following list of claims:

1. (Currently amended) A method for forming in monolithic form a DRAM-type memory, including the steps of:

forming, on a single-crystal semiconductor substrate, parallel strips including a lower insulating layer, a strongly-conductive layer, a single-crystal semiconductor layer, and an upper insulating layer;

forming, perpendicularly to the parallel strips, in the upper insulating layer and in at least a portion of the single-crystal semiconductor layer, first and second parallel trenches, each of the first and second parallel trenches being shared by neighboring cells;

forming, in each of the first parallel trenches, a first conductive line according to a strip width;

B forming, in each of the second parallel trenches, a pair of second distinct parallel conductive lines, insulated from the layers peripheral to the second parallel trench;

filling the first and second parallel trenches with an insulating material;

removing the remaining portions of the upper insulating layer; and

depositing a conductive layer,

wherein the first and second parallel trenches are formed in the upper insulating layer and at least a portion of the single-crystal semiconductor layer so that the first parallel trenches have a minimum width, and the second parallel trenches have a width which is twice that of the first parallel trenches, two neighboring parallel trenches being separated by a minimum interval, each parallel first trench being surrounded with two second parallel trenches and each second trench being surrounded with two first parallel trenches.

2. (Currently amended) The method of claim 1, wherein the forming of the parallel strips includes the steps of:

forming on a first single-crystal semiconductor substrate a single-crystal semiconductor layer resting on a first insulating layer;